



ATTORNEY DOCKET NO. 60188-116
PATENT

#8/2E.
6/10/3
Sunder

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Hiroaki NAKAOKA, et al.

Serial No.: 10/028,803

Filed: December 28, 2001

For: SEMICONDUCTOR DEVICE AND METHOD
FOR FABRICATING THE SAME

) Group Art Unit: 2811

) Examiner: SHOUXIANG HU

ELECTION UNDER 35 U.S.C. § 121

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

RECEIVED
JUN - 5 2003
TECHNOLOGY CENTER 2800

Sir:

In response to the restriction requirement set forth in the Office Action mailed May 1, 2003, having a shortened statutory period for response set to expire June 1, 2003, wherein the Examiner restricted the invention into the following distinct Species:

- Species 1 - embodiments of Figs. 1, 2 and 8, involving forming a SOI FET having lattice defect regions (or, heavily doped regions) disposed only in the channel bottom corners, and having sidewall spacers but without silicide layers;